MOSFETs Silicon Carbide N-Channel MOS

TW140N120C

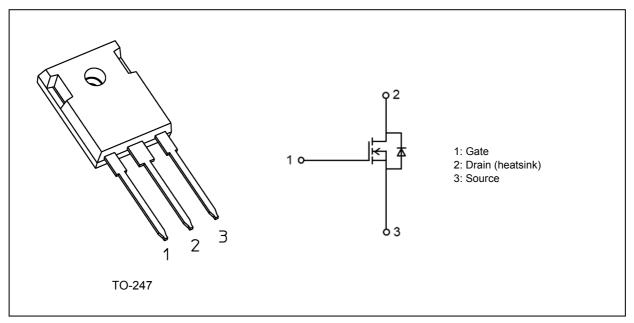
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: V_{DSF} = -1.35 V (typ.)
- (3) High voltage: $V_{DSS} = 1200 V$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 140 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1 mA)
- (6) Recommended gate source drive voltage: $V_{GS_{on}} = 18 \text{ V}, V_{GS_{off}} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

	Characteristics	Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	1200	V
Gate-source voltage		V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	Ι _D	20	A
Drain current (DC)	(T _c = 100°C)	Ι _D	13	
Drain current (pulsed)	(T _c = 25 °C)	I _{DP}	40	
Drain current (pulsed)	(T _c = 100°C)	I _{DP}	30	
Power dissipation	(T _c = 25°C)	PD	107	W
Channel temperature		T _{ch}	175	°C
Storage temperature		T _{stg}	-55 to 175	
Mounting torque		TOR	0.8	N·m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.395	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	V_{GS} = +25/-10 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current		I _{DSS}	V _{DS} = 1200 V, V _{GS} = 0 V		0.5	4	
			T _a = 150 °C, V _{DS} = 1200 V, V _{GS} = 0 V	—	3	—	
Drain-source breakdown voltage		V _{(BR)DSS}	I _D = 4 mA, V _{GS} = 0 V	1200		_	V
Gate threshold voltage (N	Note 2)	V _{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	_	5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 10 A		140	182	mΩ
			T _a = 150 °C, V _{GS} = 18 V, I _D = 10 A	—	197		

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 800 V, V _{GS} = 0 V,		691	_	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz	_	1.9	_	
Output capacitance	C _{oss}]	_	43	_	
Effective output capacitance (energy related)	C _{o(er)}		—	53	_	
Effective output capacitance (time related)	C _{o(tr)}		—	78	—	
Output charge	Q _{oss}]	_	62	_	nC
C _{oss} stored energy	E _{oss}]	_	17	_	μJ
Gate resistance	rg	V _{DS} = OPEN, f = 1 MHz	_	10	_	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	32	_	ns
Switching time (turn-on time)	t _{on}]	_	61	_	
Switching time (fall time)	t _f]	_	25	_	
Switching time (turn-off time)	t _{off}]	_	58	_	ns

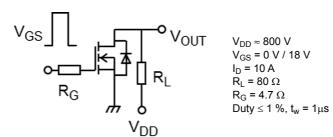


Fig. 6.2.1	Switching	Time	Test	Circuit
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6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 800 \text{ V}, \text{ V}_{GS}$ = 18 V, I _D = 10 A	_	24	—	nC
Gate-source charge 1	Q _{gs1}		_	11	_	
Gate-drain charge	Q _{gd}		_	4.2	_	

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I _{DR}	T _c = 25 °C, V _{GS} = -5 V	_	_	17	А
			T _c = 100 °C, V _{GS} = -5 V	—	_	11	
			T _c = 25 °C, V _{GS} = 18 V	_	_	20	
			T _c = 100 °C, V _{GS} = 18 V	—		13	
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V	_	-	40	
(pulsed)			T _c = 100 °C, V _{GS} = -5 V	_		14	
			T _c = 25 °C, V _{GS} = 18 V		_	40	
			T _c = 100 °C, V _{GS} = 18 V	_	_	30	
Diode forward voltage		V _{DSF}	I _{DR} = 3.5 A, V _{GS} = -5 V	_	-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 3.5 A, V _{GS} = -5 V	—	-1.70	—	
Reverse recovery time		t _{rr}	I _{DR} = 7 A, V _{GS} = 0 V,	—	43	—	ns
Reverse recovery charge		Q _{rr}	V _{DD} = 800 V, -dI _{DR} /dt = 1000 A/μs		153	_	nC
Peak reverse recovery current		Irr		—	7.1	_	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

7. Marking (Note)

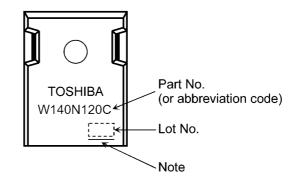
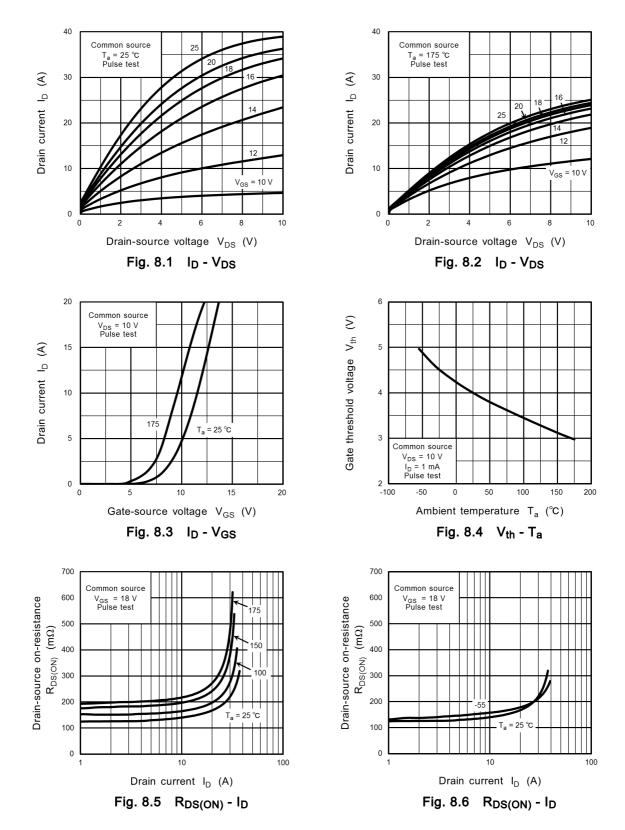


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)





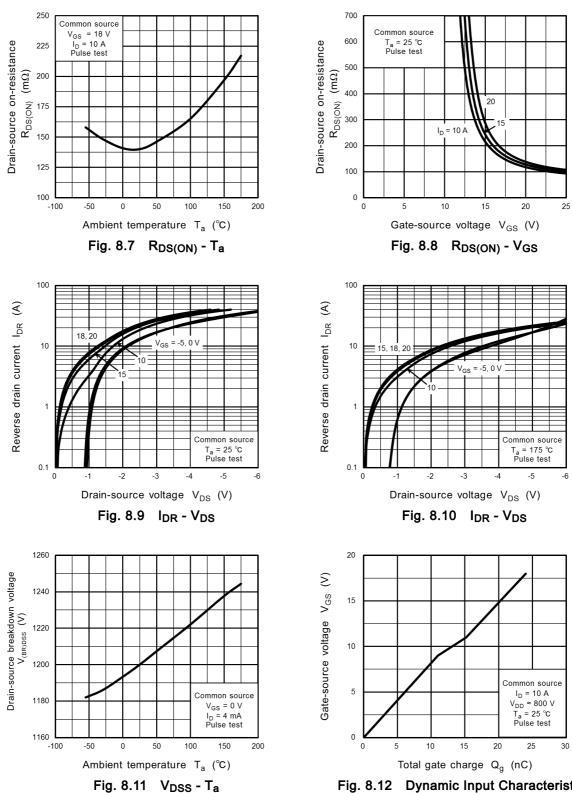
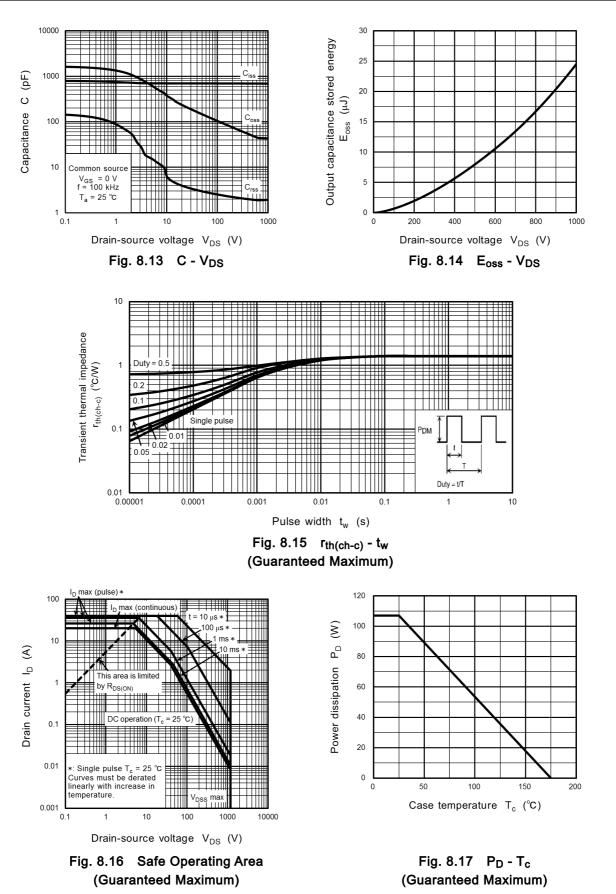
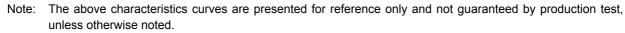


Fig. 8.12 Dynamic Input Characteristics

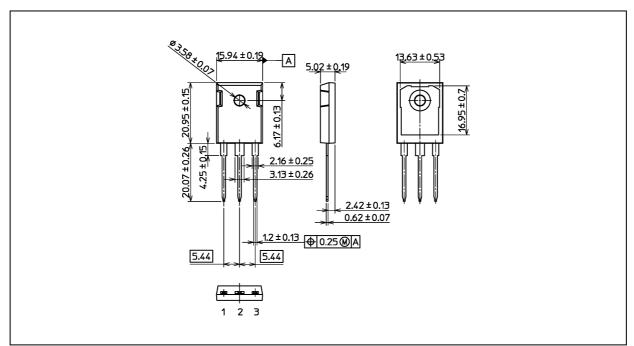






Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

	Package Name(s)
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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